



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



SOT223 NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ISSUE 3 - OCTOBER 1995

FEATURES

- * Extremely low equivalent on resistance; $R_{CE(sat)}$ **83m Ω at 3A**
- * Gain of 400 at $I_C=3$ Amps and very low saturation voltage

APPLICATIONS

- * Flash gun convertors & Battery powered circuits

PARTMARKING DETAIL – FZT688B

COMPLEMENTARY TYPE - FZT788B

ABSOLUTE MAXIMUM RATINGS.

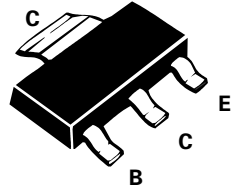
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	10	A
Continuous Collector Current	I_C	4	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	12			V	$I_C=100\mu\text{A}$
	$V_{(BR)CEO}$	12			V	$I_C=10\text{mA}^*$
	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=10\text{V}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.04	V	$I_C=0.1\text{A}, I_B=1\text{mA}$
				0.06	V	$I_C=0.1\text{A}, I_B=0.5\text{mA}^*$
				0.18	V	$I_C=1\text{A}, I_B=50\text{mA}^*$
				0.35	V	$I_C=3\text{A}, I_B=20\text{mA}^*$
				0.40	V	$I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=3\text{A}, I_B=20\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C=3\text{A}, V_{CE}=2\text{V}$
Static Forward Current Transfer Ratio	h_{FE}	500				$I_C=0.1\text{A}, V_{CE}=2\text{V}^*$
		400				$I_C=3\text{A}, V_{CE}=2\text{V}^*$
		100				$I_C=10\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	C_{ibo}		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	C_{obo}		40		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	t_{on}		40		ns	$I_C=500\text{mA}, I_{B1}=50\text{A}$
	t_{off}		500		ns	$I_{B2}=50\text{mA}, V_{CC}=10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

FZT688B



FZT688B

TYPICAL CHARACTERISTICS

